

Lattice Vibration of Layered GaTe Single Crystals

Tao Wang^{1,2*}, Qinghua Zhao^{1,2}, Yaping Miao³, Fei Ma³, Yong Xie⁴ and Wanqi Jie^{1,2}

¹ State Key Laboratory of Solidification Processing, Northwestern Polytechnical University, Xi'an, 710072, P. R. China;

² Key Laboratory of Radiation Detection Materials and Devices, Ministry of Industry and Information Technology, Xi'an, 710072, P. R. China; nwpugate@mail.nwpu.edu.cn (Q.Z.)

³ State Key Laboratory for Mechanical Behavior of Materials, Xi'an Jiaotong University, Xi'an, 710049, P. R. China; miaoyp2007@126.com (Y.M.); mafei@mail.xjtu.edu.cn (F.M.)

⁴ State Key Discipline Laboratory of Wide Band Gap Semiconductor Technology, School of Advanced Materials and Nanotechnology, Xidian University, Xi'an, 710071, P. R. China; yxie@xidian.edu.cn(Y.X.)

* Correspondence: taowang@nwpu.edu.cn (T.W.); Tel.: +86-29-88495414

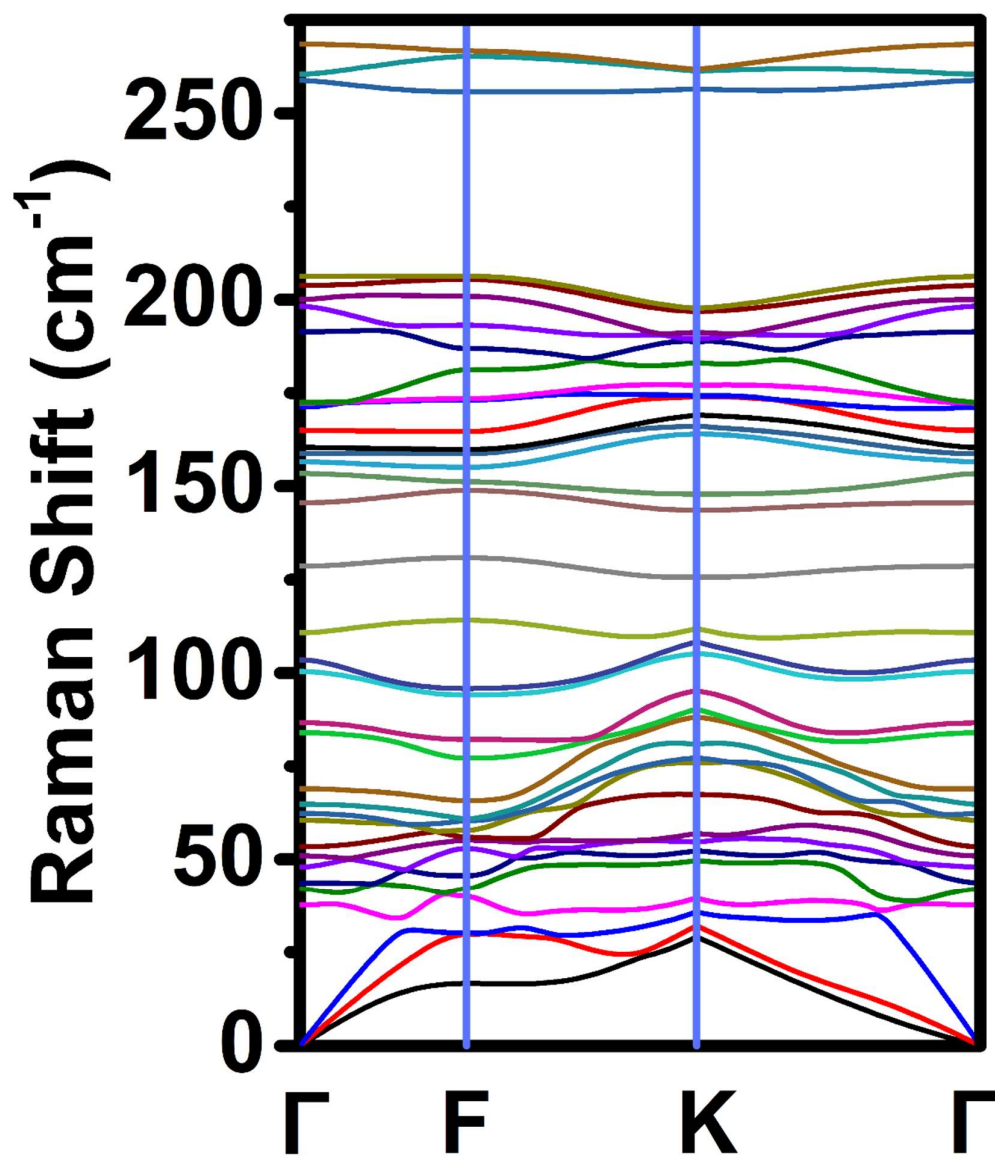


Fig. S1 The calculated Phonon dispersion of GaTe Single crystals.

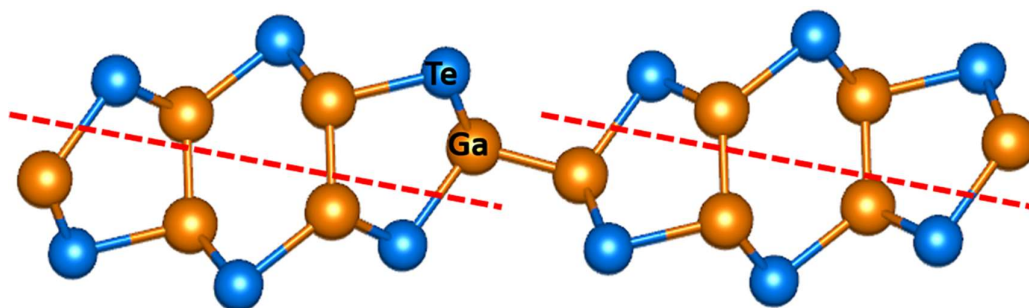


Fig. S2 The direction of axis in GaTe